## What is claimed is:

1	<ol> <li>A method for forming a double density wordline,</li> </ol>
2	comprising:
3	providing a semiconductor substrate;
4	sequentially forming a poly layer, a first insulating
5	layer, a first sacrificial layer, a second
6	insulating layer, and a photoresist layer with a
7	wordline pattern on the semiconductor substrate;
8	sequentially etching the second insulating layer and the
9	first sacrificial layer using the photoresist layer
10	as an etching mask until the first insulating layer
11	is exposed to form a first wordline mask, a second
12	wordline mask, and an opening therebetween;
13	removing the photoresist layer;
14	forming a spacer on a sidewall of the opening;
15	forming a second sacrificial layer in the opening;
16	removing the spacer, the second insulating layer, and
17	the first insulating layer under the spacer to form
18	a third wordline mask composed of the second
19	sacrificial layer and the first insulating layer
20	thereunder; and
21	etching the poly layer to form a first wordline, a second
22	wordline, and a third wordline using the first
23	wordline mask, the second wordline mask, and the
24	third wordline mask as etching masks.
1	2. The method for forming a double density wordline
2	of claim 1, further comprising a silicide layer over the surface
3	of the poly layer.

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- 1 3. The method for forming a double density wordline 2 of claim 2, wherein the silicide layer is a tungsten silicide 3 layer.
- 1 4. The method for forming a double density wordline 2 of claim 3, wherein a thickness of the tungsten silicide layer 3 is 1550 to 1650Å.
- 5. The method for forming a double density wordline of claim 1, wherein a thickness of the poly layer is 1150 to 1250Å.
- 1 6. The method for forming a double density wordline 2 of claim 1, wherein the first insulating layer is a silicon 3 oxide layer.
- 7. The method for forming a double density wordline of claim 6, wherein a thickness of the silicon oxide layer is 750 to 850Å.

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- 8. The method for forming a double density wordline of claim 1, wherein the first sacrificial layer is a poly layer.
- 9. The method for forming a double density wordline of claim 8, wherein a thickness of the poly layer is 950 to 1050Å.
- 1 10. The method for forming a double density wordline 2 of claim 1, wherein the second insulating layer is a nitride 3 layer.

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1,	11. The method for forming a double density wordline
2	of claim 10, wherein a thickness of the nitride layer is 250
3	to 350Å.
1	12. The method for forming a double density wordline
2	of claim 1, wherein the spacer is a nitride layer.
1	13. The method for forming a double density wordline
2	of claim 1, wherein the second sacrificial layer is a poly
3	layer.
1	14. A method for forming a double density wordline,
2	comprising:
3	providing a semiconductor substrate with a poly layer,
4	a silicide layer, a oxide layer, a first dummy poly
5	layer, and a first nitride layer;
6	forming a photoresist layer with a first opening on the
7	nitride layer, wherein a portion of the first nitride
8	layer is exposed by the first opening;
9	sequentially etching the fist nitride layer and the first
10	dummy poly layer until the oxide layer is exposed
11	to form a first wordline mask, a second wordline
12	mask, and a second opening therebetween;
13	removing the photoresist layer;
14	conformably forming a second nitride layer cover the first
15	wordline mask, the second wordline mask, and the
16	second opening;
17	anisotropically etching the second nitride layer to form
18	a spacer on a sidewall of the second opening;
19	forming a second dummy poly layer cover the first wordline
20	mask, the second wordline mask, and the second

21	opening, wherein the second opening is filled with
22	the second dummy poly layer;
23	etching the second dummy poly layer to a level below the
24	spacer;
25	removing the spacer, the first nitride layer, and the
26	exposing oxide layer to form a third wordline mask
27	composes of the second dummy poly layer and the oxide
28	thereunder; and
29	sequentially etching the silicide layer and the poly layer
30	to form a first wordline, a second wordline, a third
31	wordline using the first wordline mask, the second
32	wordline mask, and the third wordline mask as etching
33	masks.
1	15. The method for forming a double density wordline
2	of claim 14, further comprising a step to remove the first
3	wordline mask, the second wordline mask, and the third wordline
4	mask.
-	mask.
1	16. The method for forming a double density wordline
2	of claim 14, wherein a thickness of the poly layer is 1150
3	to 1250Å.
1	17. The method for forming a double density wordline
2	of claim 14, wherein the silicide layer is a tungsten silicide
3	layer.
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1	18. The method for forming a double density wordline
2	of claim 17, wherein a thickness of the tungsten silicide layer
3	is 1550 to 1650Å.

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- 1 19. The method for forming a double density wordline 2 of claim 14, wherein a thickness of the oxide layer is 750 3 to 850Å.
- 20. The method for forming a double density wordline of claim 14, wherein a thickness of the first dummy poly layer is 950 to 1050Å.
  - 21. The method for forming a double density wordline of claim 14, wherein a thickness of the first nitride layer is 250 to 350Å.
- 1 22. The method for forming a double density wordline 2 of claim 14, wherein a thickness of the second nitride layer 3 is 400Å.
- 1 23. The method for forming a double density wordline 2 of claim 14, wherein the anisotropic etching is reactive ion 3 etching or plasma etching.
- 1 24. The method for forming a double density wordline 2 of claim 14, wherein a thickness of the second dummy poly layer 3 is 2000Å.